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(54) **PREFERRED METHODS FOR PRODUCING ELECTRICAL CIRCUIT ELEMENTS USED TO CONTROL AN ELECTRONIC DISPLAY**

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(51) **Int. Cl.**[7] **H01L 21/00**

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(58) **Field of Search** 438/21, 22, 38; 347/40, 43, 70

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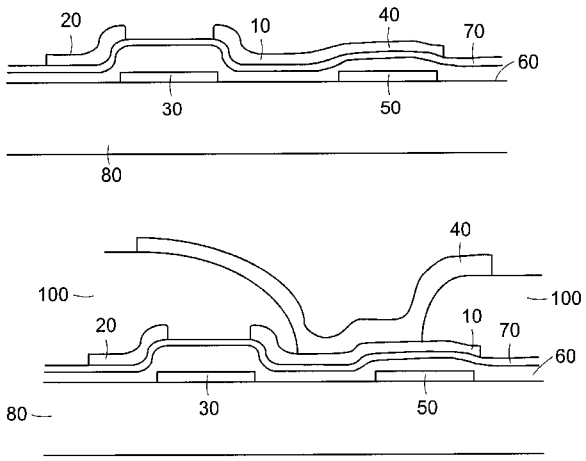
(57) **ABSTRACT**

Systems and methods for producing thin film transistor structures useful in controlling electronic displays. Thin film transistors are fabricated using all-additive methods including printing techniques, soft lithography and material deposition methods. The thin film transistors can be deposited with the gate on the bottom or on the top of the structure. The deposition methods include the possibility of isolating nearly completely the transistor structure from the electronic display devices, so as to minimize or eliminate deleterious interactions therebetween.

26 Claims, 4 Drawing Sheets